

Amendments to the Specification

Please replace paragraph [0018] with the following amended paragraph:

[0018] Creation of the source region (302) can be accomplished at multiple points within the fabrication sequence. FIG. 3a illustrates a cross-section of the device (300) with the center part of the substrate (304) covered only by the coupling oxide (306). It is possible to fabricate a source (302) by means of anisotropic ion implantation (308). However, if the device were subjected to ion implant at this state, parts of the coupling oxide (306) would be damaged by being exposed to high-energy ions (308). The addition of ions into these sections will reduce their dielectric strength, causing leak paths (312) from the floating gate to the source.

Please replace paragraph [0025] with the following amended paragraph:

[0025] As a result of the pullback process, the floating gate (404) and its leading edge (428) are no longer aligned with the 2nd oxide (408) and will be farther from the control gate than in a typical device. The leading edge (428) of the floating gate (404) is also farther from the edge of the second opening (412) than in a typical device. As a result also, the effective footprint of the coupling oxide (426) is farther from the narrowest region of the first opening [(412)] (410).

Please replace paragraph [0028] with the following amended paragraph:

[0028] FIG. 4e illustrates an anisotropic etch process performed on the device according to one example of the present invention [[disclosure]]. This etch process removes a third oxide, i.e., the spacer oxide (436) from over the silicon nitride dielectric (406) and forms a third opening by removing a portion of spacer oxide (436) and the coupling oxide (402) from the second opening (416) and exposes the source (432).